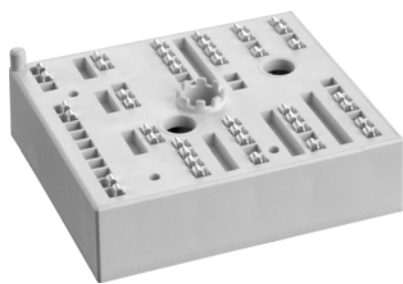


SKiiP 29TMLI12F4V1



MiniSKiiP® 2

3-Level TNPC IGBT-Module

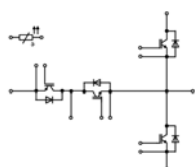
SKiiP 29TMLI12F4V1

Features*

- Fast Trench 4 IGBTs
- Trench IGBTs
- Robust and soft diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

Remarks*

- Case temperature limited to $T_C=125^{\circ}\text{C}$ max.; $T_C = T_S$ (for baseplateless modules)
- Product reliability results valid for $T_J \leq 150^{\circ}\text{C}$ (recommended $T_{Jop} = -40 \dots +150^{\circ}\text{C}$)
- IGBT 1: outer IGBTs T1&T4
- IGBT 2: inner IGBTs T2&T3
- Diode 1: outer diodes D1&D4
- Diode 2: inner diodes D2&D3

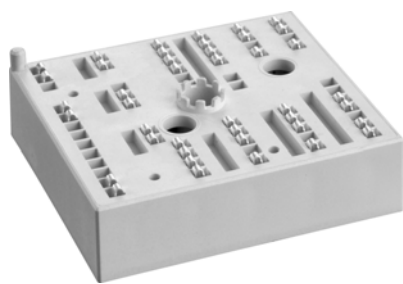


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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT1				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	144	A
	T _j = 175 °C	T _s = 70 °C	115	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	172	A
	T _j = 175 °C	T _s = 70 °C	138	A
I _{Cnom}			150	A
I _{CRM}	I _{CRM} = 3 x I _{Cnom}		450	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V, V _{GE} ≤ 15 V, T _j = 150 °C, V _{CES} ≤ 1200 V		6	μs
T _j			-40 ... 175	°C
IGBT2				
V _{CES}	T _j = 25 °C		650	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	131	A
	T _j = 175 °C	T _s = 70 °C	104	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	150	A
	T _j = 175 °C	T _s = 70 °C	120	A
I _{Cnom}			150	A
I _{CRM}	I _{CRM} = 3 x I _{Cnom}		450	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 360 V, V _{GE} ≤ 15 V, T _j = 150 °C, V _{CES} ≤ 650 V		6	μs
T _j			-40 ... 175	°C
Diode1				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	148	A
	T _j = 175 °C	T _s = 70 °C	117	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	170	A
	T _j = 175 °C	T _s = 70 °C	136	A
I _{Fnom}			150	A
I _{FRM}	I _{FRM} = 3 x I _{Fnom}		450	A
I _{FSM}	10 ms, sin 180°, T _j = 25 °C		774	A
T _j			-40 ... 175	°C
Diode2				
V _{RRM}	T _j = 25 °C		650	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	129	A
	T _j = 175 °C	T _s = 70 °C	99	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	155	A
	T _j = 175 °C	T _s = 70 °C	121	A
I _{Fnom}			150	A
I _{FRM}	I _{FRM} = 2 x I _{Fnom}		300	A
I _{FSM}	10 ms, sin 180°, T _j = 25 °C		1200	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}			100	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50 Hz, t = 1 min		2500	V

SKiIP 29TMLI12F4V1



MiniSKiIP® 2

3-Level TNPC IGBT-Module

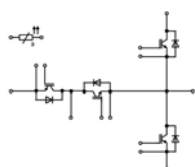
SKiIP 29TMLI12F4V1

Features*

- Fast Trench 4 IGBTs
- Trench IGBTs
- Robust and soft diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

Remarks*

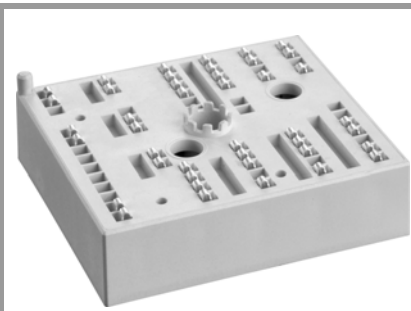
- Case temperature limited to $T_C=125^\circ\text{C}$ max.; $T_C = T_S$ (for baseplateless modules)
- Product reliability results valid for $T_J \leq 150^\circ\text{C}$ (recommended $T_{Jop} = -40 \dots +150^\circ\text{C}$)
- IGBT 1: outer IGBTs T1&T4
- IGBT 2: inner IGBTs T2&T3
- Diode 1: outer diodes D1&D4
- Diode 2: inner diodes D2&D3



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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT1						
V _{CE(sat)}	I _C = 150 A	T _J = 25 °C		2.05	2.42	V
	V _{GE} = 15 V chiplevel	T _J = 150 °C		2.59	2.96	V
V _{CE0}	chiplevel	T _J = 25 °C		1.10	1.28	V
		T _J = 150 °C		0.95	1.13	V
r _{CE}	V _{GE} = 15 V	T _J = 25 °C		6.3	7.6	mΩ
	chiplevel	T _J = 150 °C		11	12	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 5.2 mA		5.2	5.8	6.4	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 1200 V, T _J = 25 °C				0.3	mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		8.80		nF
C _{oes}		f = 1 MHz		0.58		nF
C _{res}		f = 1 MHz		0.47		nF
Q _G	V _{GE} = - 8 V...+ 15 V			850		nC
R _{Gint}	T _J = 25 °C			5.0		Ω
t _{d(on)}	V _{CE} = 300 V	T _J = 150 °C		155		ns
t _r	I _C = 150 A	T _J = 150 °C		54		ns
E _{on}	V _{GE} = +15/-15 V	T _J = 150 °C		5.2		mJ
t _{d(off)}	R _{G on} = 1.6 Ω	T _J = 150 °C		323		ns
t _f	R _{G off} = 1.6 Ω	T _J = 150 °C		66		ns
E _{off}	di/dt _{on} = 2550 A/μs di/dt _{off} = 1850 A/μs	T _J = 150 °C		6.1		mJ
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(mK)			0.35		K/W
R _{th(j-s)}	per IGBT, λ _{paste} =2.5 W/(mK)			0.26		K/W
IGBT2						
V _{CE(sat)}	I _C = 150 A	T _J = 25 °C		1.45	1.77	V
	V _{GE} = 15 V chiplevel	T _J = 150 °C		1.70	2.10	V
V _{CE0}	chiplevel	T _J = 25 °C		0.90	1.00	V
		T _J = 150 °C		0.82	0.90	V
r _{CE}	V _{GE} = 15 V	T _J = 25 °C		3.7	5.1	mΩ
	chiplevel	T _J = 150 °C		5.9	8.0	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 2.4 mA		5.1	5.8	6.4	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 650 V, T _J = 25 °C				0.3	mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		9.24		nF
C _{oes}		f = 1 MHz		0.60		nF
C _{res}		f = 1 MHz		0.27		nF
Q _G	V _{GE} = - 8 V...+ 15 V			1360		nC
R _{Gint}	T _J = 25 °C			2.0		Ω
t _{d(on)}	V _{CE} = 300 V	T _J = 150 °C		118		ns
t _r	I _C = 150 A	T _J = 150 °C		40		ns
E _{on}	V _{GE} = +15/-15 V	T _J = 150 °C		1.6		mJ
t _{d(off)}	R _{G on} = 1.6 Ω	T _J = 150 °C		276		ns
t _f	R _{G off} = 1.6 Ω	T _J = 150 °C		79		ns
E _{off}	di/dt _{on} = 3900 A/μs di/dt _{off} = 1650 A/μs	T _J = 150 °C		6.1		mJ
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(mK)			0.57		K/W
R _{th(j-s)}	per IGBT, λ _{paste} =2.5 W/(mK)			0.46		K/W

SKiiP 29TMLI12F4V1



MiniSKiiP® 2

3-Level TNPC IGBT-Module

SKiiP 29TMLI12F4V1

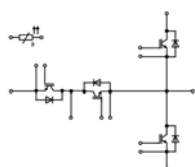
Features*

- Fast Trench 4 IGBTs
- Trench IGBTs
- Robust and soft diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

Remarks*

- Case temperature limited to $T_C=125^\circ\text{C}$ max.; $T_C = T_S$ (for baseplateless modules)
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{jop} = -40 \dots +150^\circ\text{C}$)
- IGBT 1: outer IGBTs T1&T4
- IGBT 2: inner IGBTs T2&T3
- Diode 1: outer diodes D1&D4
- Diode 2: inner diodes D2&D3

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Diode1						
V _F = V _{EC}	I _F = 150 A	T _j = 25 °C		2.17	2.49	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.11	2.42	V
V _{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
		T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		5.8	6.6	mΩ
		T _j = 150 °C		8.1	8.8	mΩ
I _{RRM}	I _F = 150 A	T _j = 150 °C		191.3		A
Q _{rr}	di/dt _{off} = 3760 A/μs	T _j = 150 °C		26		μC
E _{rr}	V _R = 300 V	T _j = 150 °C		6.5		mJ
	V _{GE} = +15/-15 V					
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			0.45		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			0.36		K/W
Diode2						
V _F = V _{EC}	I _F = 150 A	T _j = 25 °C		1.40	1.76	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		1.39	1.77	V
V _{F0}	chiplevel	T _j = 25 °C		1.04	1.24	V
		T _j = 150 °C		0.85	0.99	V
r _F	chiplevel	T _j = 25 °C		2.4	3.5	mΩ
		T _j = 150 °C		3.6	5.2	mΩ
I _{RRM}	I _F = 150 A	T _j = 150 °C		131.4		A
Q _{rr}	di/dt _{off} = 2640 A/μs	T _j = 150 °C		13.5		μC
E _{rr}	V _R = 300 V	T _j = 150 °C		2.4		mJ
	V _{GE} = +15/-15 V					
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			0.73		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			0.56		K/W
Module						
L _{sCE1}				-		nH
L _{CE}				-		nH
R _{CC'+EE'}		T _s = 25 °C		-		mΩ
		T _s = 125 °C		-		mΩ
M _s	to heat sink		2		2.5	Nm
M _t			-			Nm
w				55		g
Temperature Sensor						
R ₁₀₀	T _r =100°C (R ₂₅ =1000Ω)			1670 ± 3%		Ω
R(T)	R(T)=1000Ω[1+A(T-25°C)+B(T-25°C) ²] , A = 7.635*10 ⁻³ °C ⁻¹ , B = 1.731*10 ⁻⁵ °C ⁻²					



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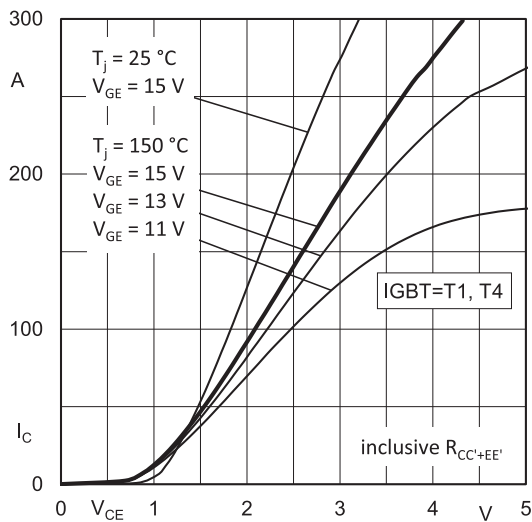


Fig. 1: Typ. IGBT1 output characteristic, incl. $R_{CC'+EE'}$

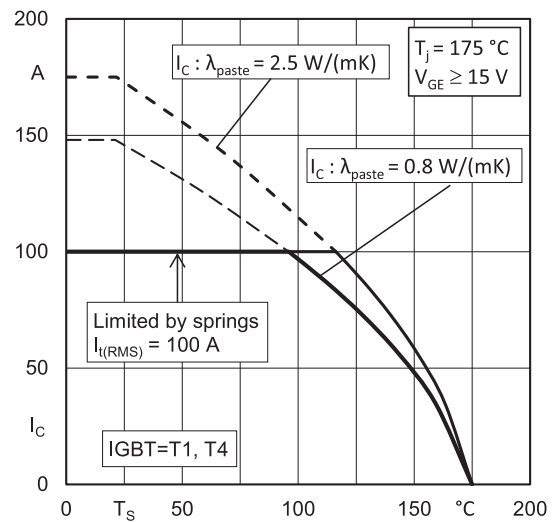


Fig. 2: IGBT1 rated current vs. Temperature $I_C=f(T_s)$

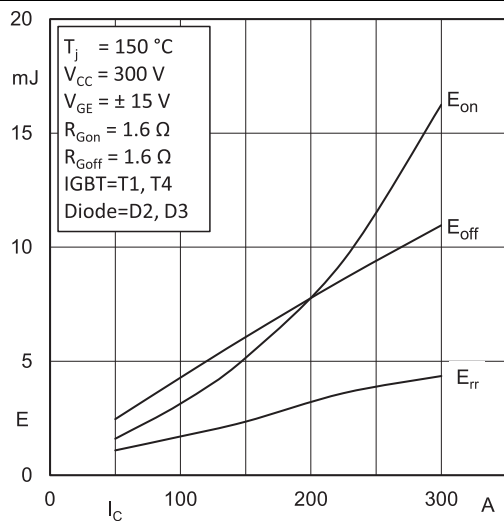


Fig. 3: Typ. IGBT1 & Diode2 turn-on /-off energy = $f(I_C)$

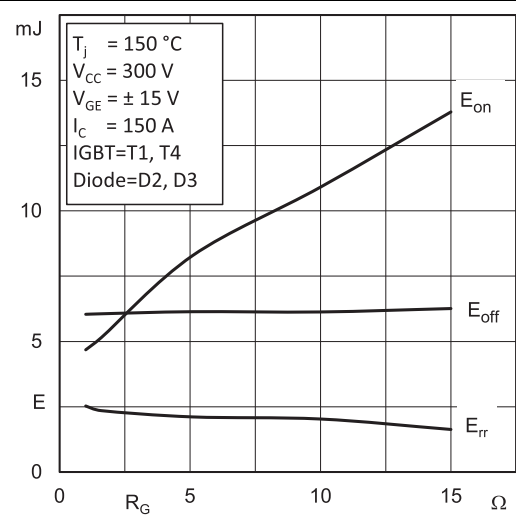


Fig. 4: Typ. IGBT1 & Diode2 turn-on /-off energy = $f(R_G)$

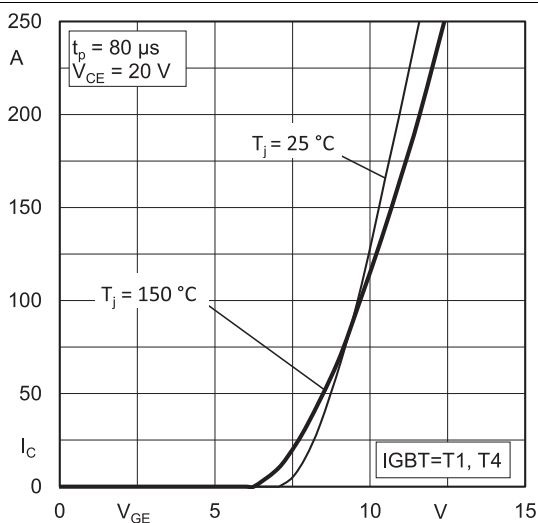


Fig. 5: Typ. IGBT1 transfer characteristic

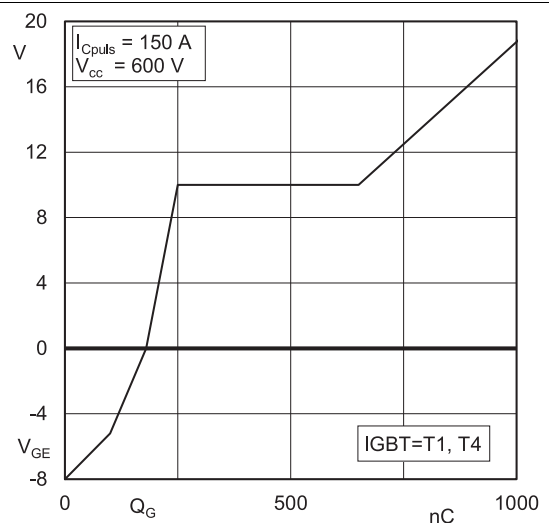


Fig. 6: Typ. IGBT1 gate charge characteristic

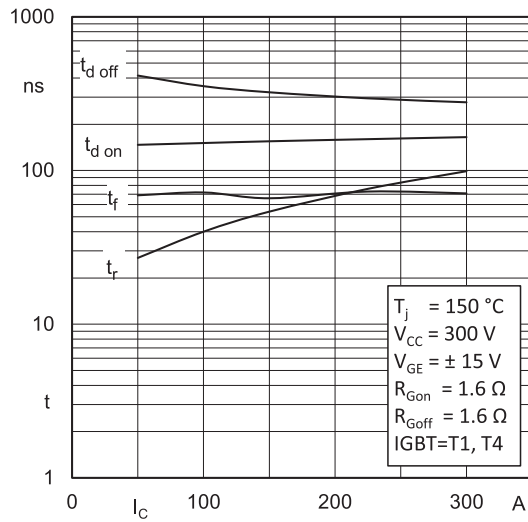


Fig. 7: Typ. IGBT1 switching times vs. I_C

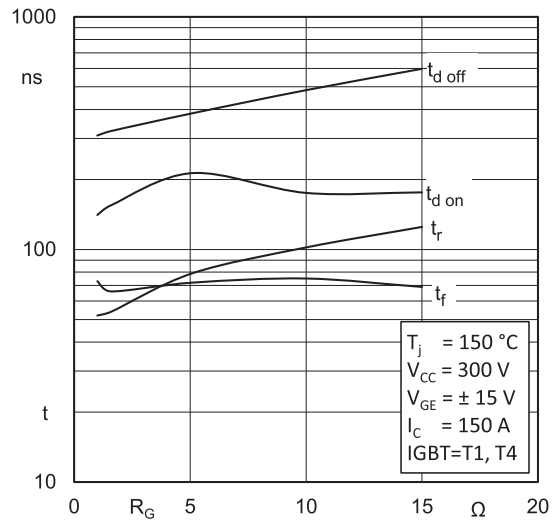


Fig. 8: Typ. IGBT1 switching times vs. gate resistor R_G

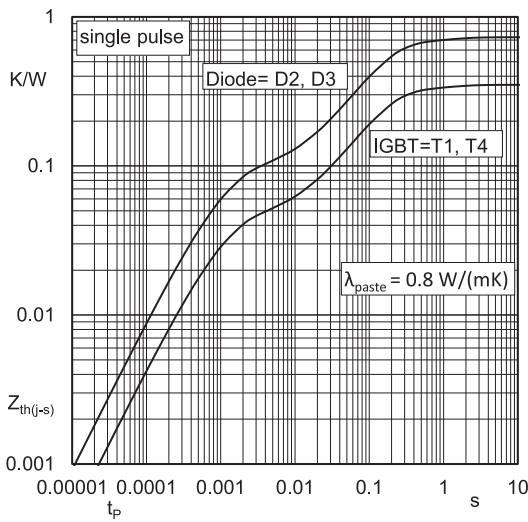


Fig. 9: Transient thermal impedance of IGBT1 & Diode2

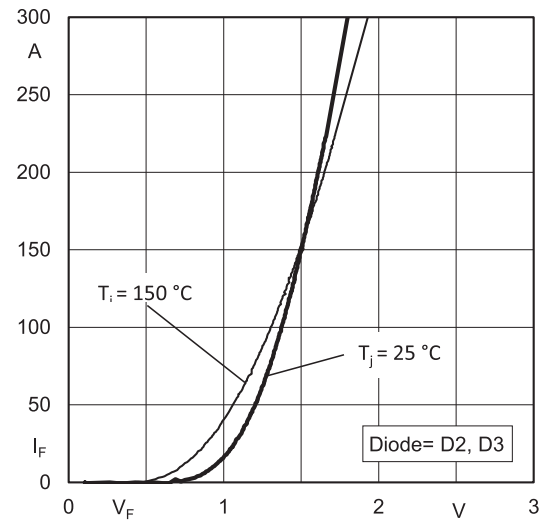


Fig. 10: Typ. Diode2 forward characteristic, incl. $R_{CC'} + EE'$

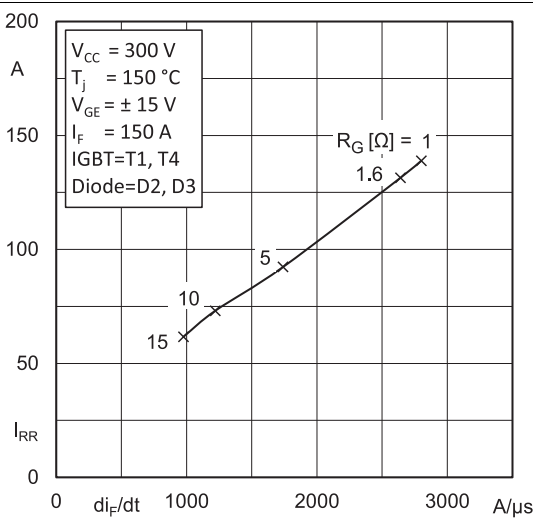


Fig. 11: Typ. Diode2 peak reverse recovery current

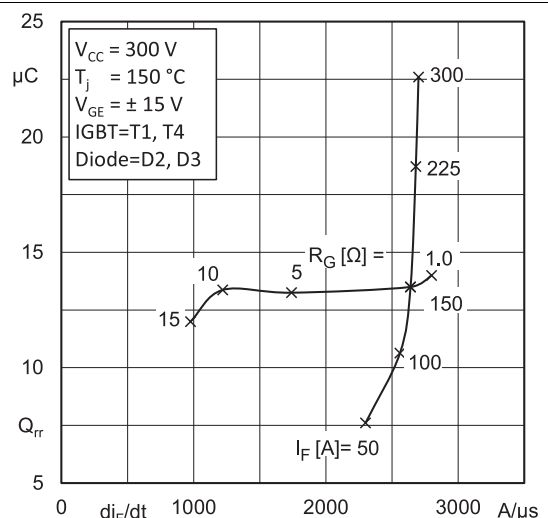


Fig. 12: Typ. Diode2 recovery charge

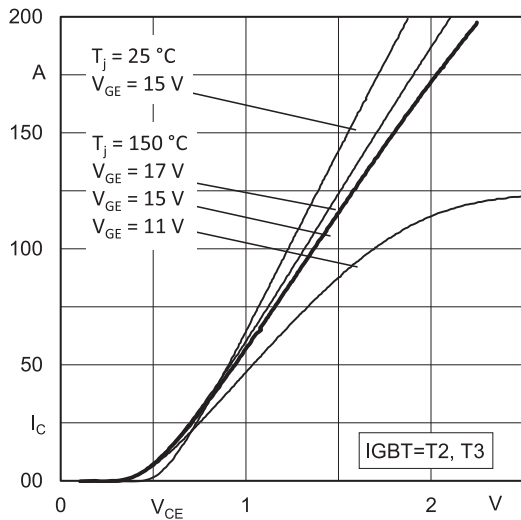


Fig. 13: Typ. IGBT2 output characteristic, incl. $R_{CC'+EE'}$

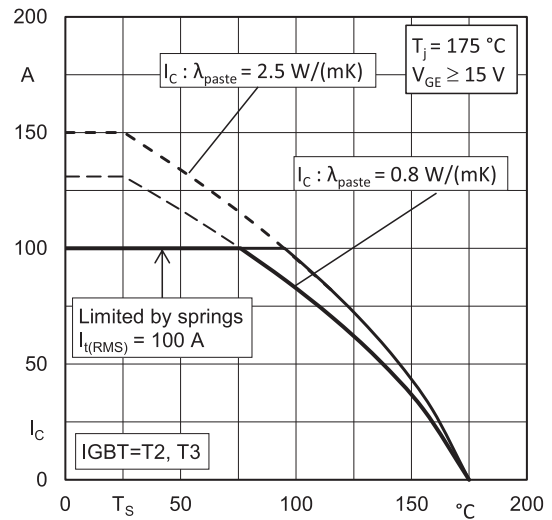


Fig. 14: IGBT2 Rated current vs. Temperature $I_C = f(T_s)$

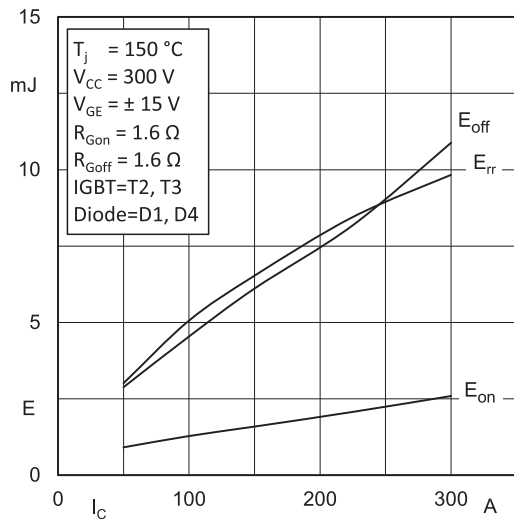


Fig. 15: Typ. IGBT2 & Diode1 turn-on /-off energy = $f(I_C)$

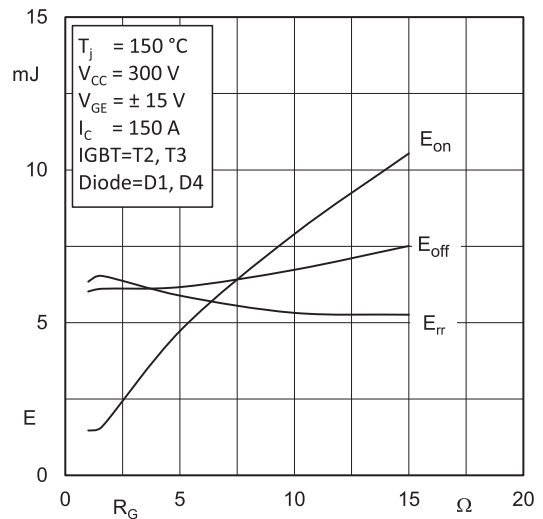


Fig. 16: Typ. IGBT2 & Diode1 turn-on /-off energy = $f(R_G)$

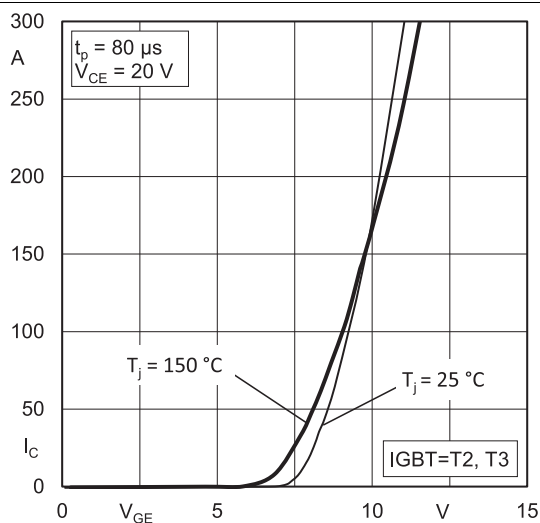


Fig. 17: Typ. IGBT2 transfer characteristic

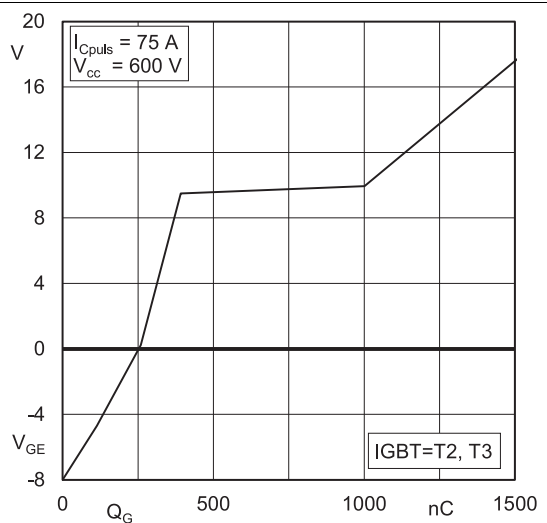


Fig. 18: Typ. IGBT2 gate charge characteristic

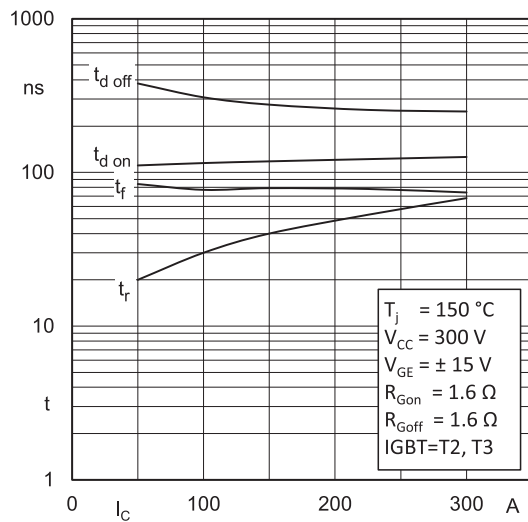


Fig. 19: Typ. IGBT2 switching times vs. I_C

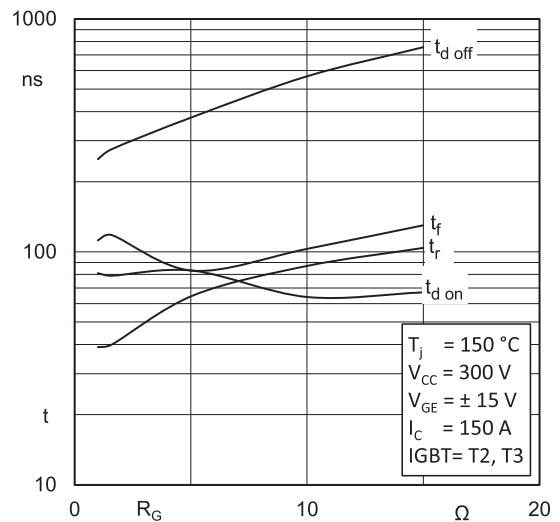


Fig. 20: Typ. IGBT2 switching times vs. gate resistor R_G

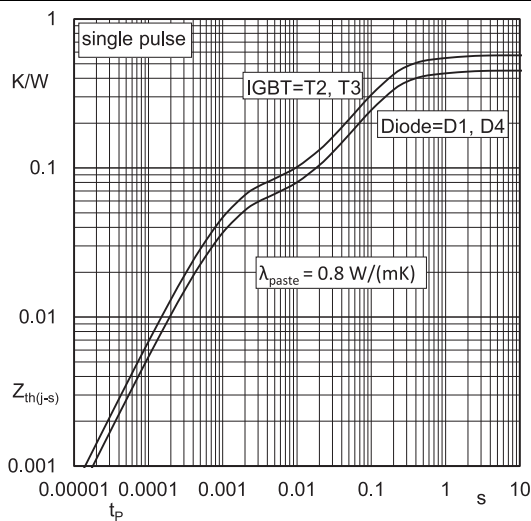


Fig. 21: Transient thermal impedance of IGBT2 & Diode1

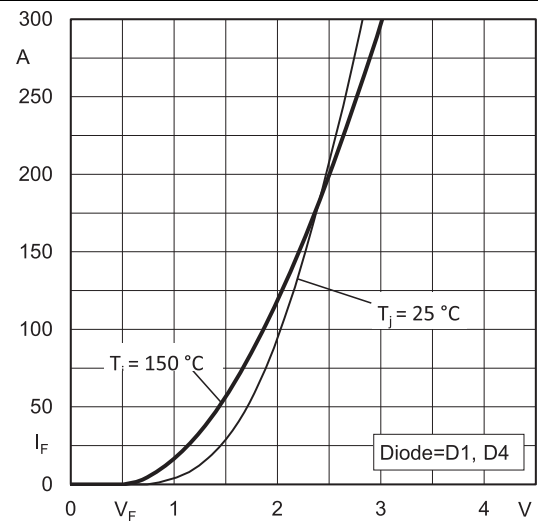


Fig. 22: Typ. Diode1 forward characteristic, incl. $R_{CC'} + EE'$

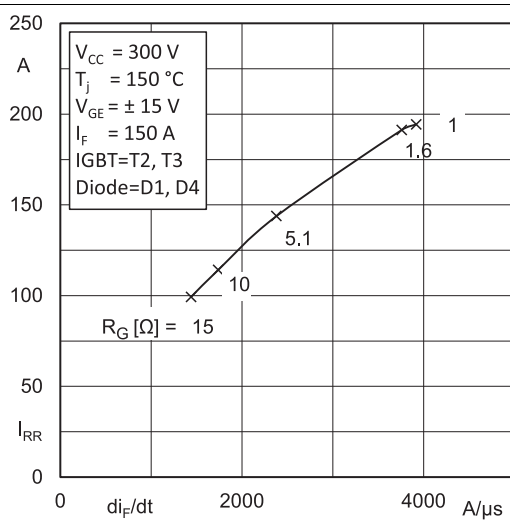


Fig. 23: Typ. Diode1 peak reverse recovery current

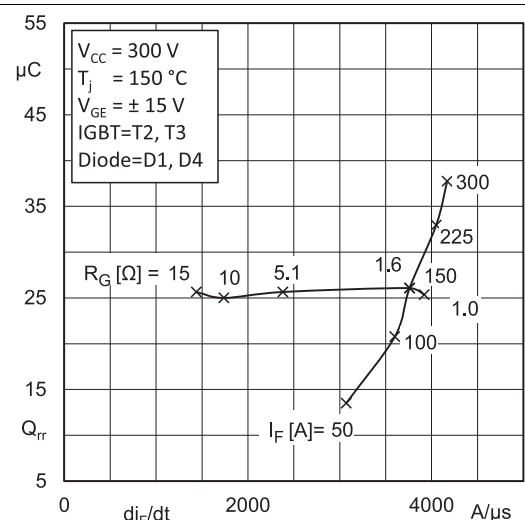
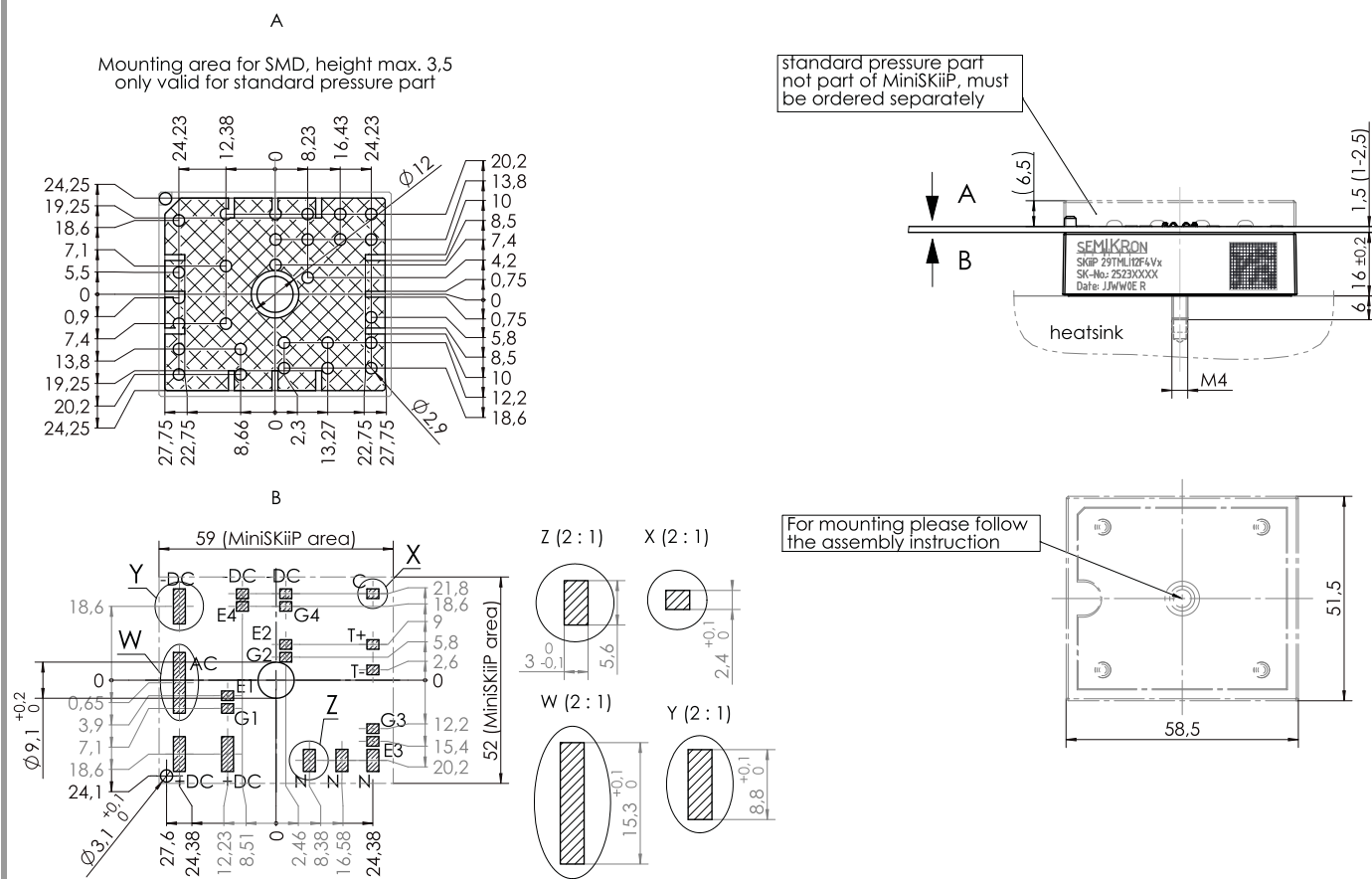
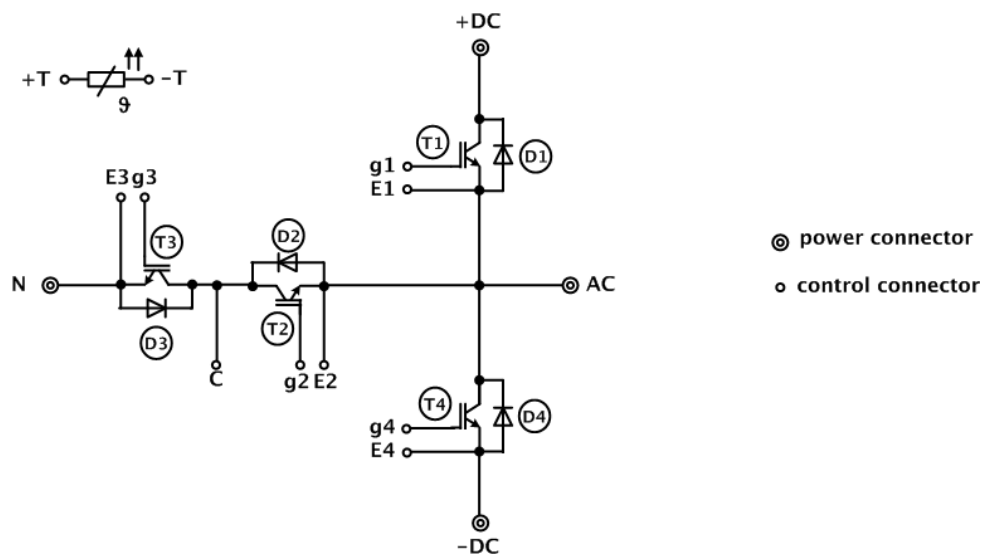


Fig. 24: Typ. Diode1 recovery charge



pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

***IMPORTANT INFORMATION AND WARNINGS**

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